

# 2N3442 Silicon NPN Transistor High Power Industrial TO-3 Type Package

#### **Description:**

The 2N3442 is a silicon NPN power transistor in a TO-3 type package designed for applications in industrial and commercial equipment including high fidelity audio amplifiers, series and shunt regulators and power switches.

#### Features:

- Collector–Emitter Sustaining Voltage: V<sub>CEO(sus)</sub> = 140V Min
- Excellent Second Breakdown Capability

**Absolute Maximum Ratings:** 

Collector–Emitter Voltage, V <sub>CEO</sub>	140V
Collector–Base Voltage, V <sub>CBO</sub>	
Emitter-Base Voltage, V <sub>EB</sub>	7V
Collector Current, I <sub>C</sub>	
Continuous	10A
Peak	15A
Total Power Dissipation (T <sub>C</sub> = +25°C), P <sub>D</sub>	
Derate Above 25°C	0.67W/°C
Operating Junction Temperature Range, T <sub>J</sub>	. −65° to +200°C
Storage Temperature Range, T <sub>stq</sub>	. −65° to +200°C
Thermal Resistance, Junction-to-Case, RthJC	1.5°C/W

### **<u>Electrical Characteristics:</u>** (T<sub>C</sub> = +25°C unless otherwise specified)

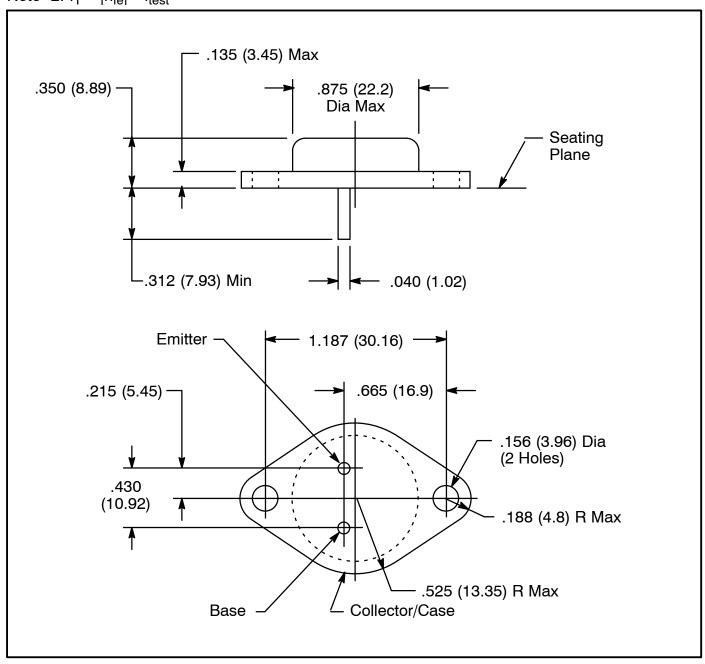
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit			
OFF Characteristics									
Collector-Emitter Sustaining Voltage	V <sub>CEO(sus)</sub>	I <sub>C</sub> = 200mA, I <sub>B</sub> = 0	140	_	_	V			
Collector Cutoff Current	I <sub>CEO</sub>	$V_{CE} = 140V, I_B = 0$	_	_	200	mA			
	I <sub>CEX</sub>	$V_{CE} = 140V, V_{BE(off)} = 1.5V$	_	_	5	mA			
		$V_{CE} = 140V, V_{BE(off)} = 1.5V, T_{C} = +150^{\circ}C$	_	_	30	mA			
Emitter Cutoff Current	I <sub>EBO</sub>	$V_{BE} = 7V$ , $I_C = 0$	_	_	5	mΑ			

# **<u>Electrical Characteristics (Cont'd):</u>** $(T_C = +25^{\circ}C \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit			
ON Characteristics (Note 1)									
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 4V, I <sub>C</sub> = 3A	20	_	70				
		V <sub>CE</sub> = 4V, I <sub>C</sub> = 10A	7.5	_	_				
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 10A, I <sub>B</sub> = 2A	_	_	5	V			
Base-Emitter On Voltage	V <sub>BE(on)</sub>	V <sub>CE</sub> = 4V, I <sub>C</sub> = 10A	_	_	5.7	V			
Dynamic Characteristics	•				•				
Current Gain-Bandwidth Product	f <sub>T</sub>	$V_{CE} = 4V$ , $I_{C} = 2A$ , $f_{test} = 40$ kHz, Note 2	80	_	_	kHz			
Small-Signal Current Gain	h <sub>fe</sub>	$V_{CE}$ = 4V, $I_{C}$ = 2A, $f_{test}$ = 1kHz	12	_	72				

Note 1. Pulse Test: Pulse Width =  $300\mu s$ , Duty Cycle  $\leq 2\%$ .

Note 2.  $f_T = |h_{fe}| \cdot f_{test}$ 



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